July 2000

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FDP6030BL/FDB6030BL



FDP6030BL/FDB6030BL N-Channel Logic Level PowerTrench[®] MOSFET

General Description

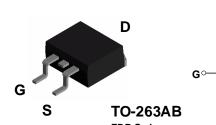
Features

This N-Channel Logic Level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{\scriptscriptstyle DS(on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

- 40 A, 30 V. $R_{DS(ON)} = 0.018 \ \Omega @ V_{GS} = 10 \ V R_{DS(ON)} = 0.024 \ \Omega @ V_{GS} = 4.5 \ V.$
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low R_{DS(ON)}.
- 175°C maximum junction temperature rating.





FDB Series

Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter	FDP6030BL	FDB6030BL	Units
V _{DSS}	Drain-Source Voltage	30		V
V _{GSS}	Gate-Source Voltage	±20		V
ID	Maximum Drain Current - Continuous (Note 1) 40		10	А
	- Pulsed	1	20	
PD	Total Power Dissipation @ $T_c = 25^{\circ}C$	60		W
	Derate above 25°C	0.36		W/°C
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-65 to +175		°C
Therma	I Characteristics			
RθJC	Thermal Resistance, Junction-to-Case	2.5		°C/W
RθJA	Thermal Resistance, Junction-to-Ambient	62.5		°C/W

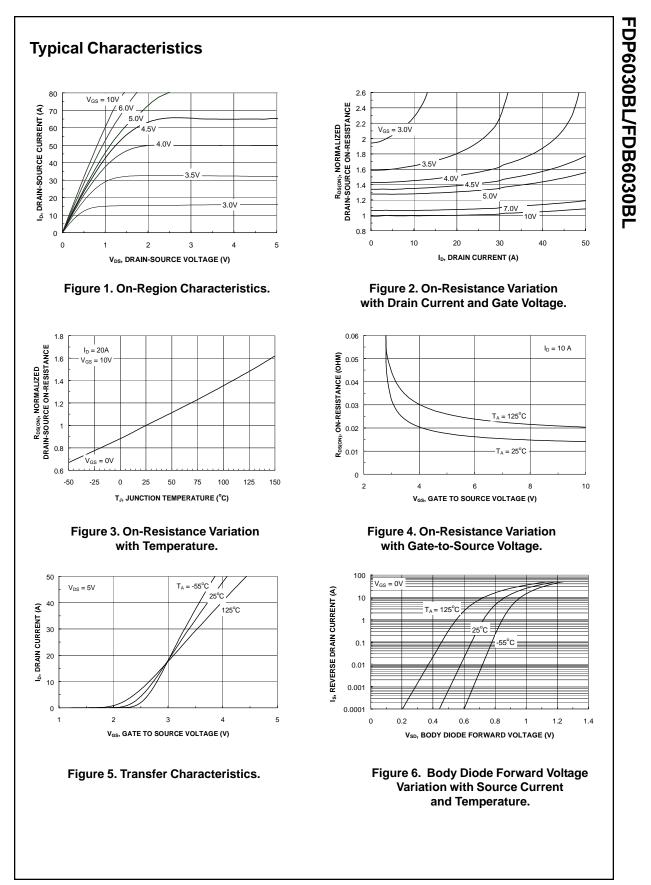
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB6030BL	FDB6030BL	13"	24mm	800
FDP6030BL	FDP6030BL	Tube	N/A	45

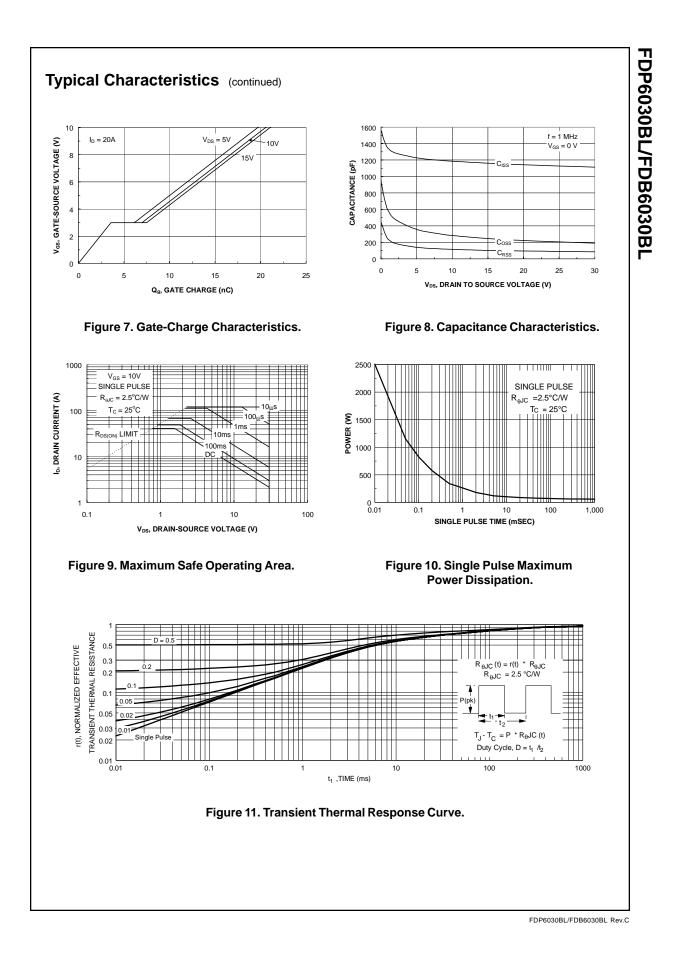
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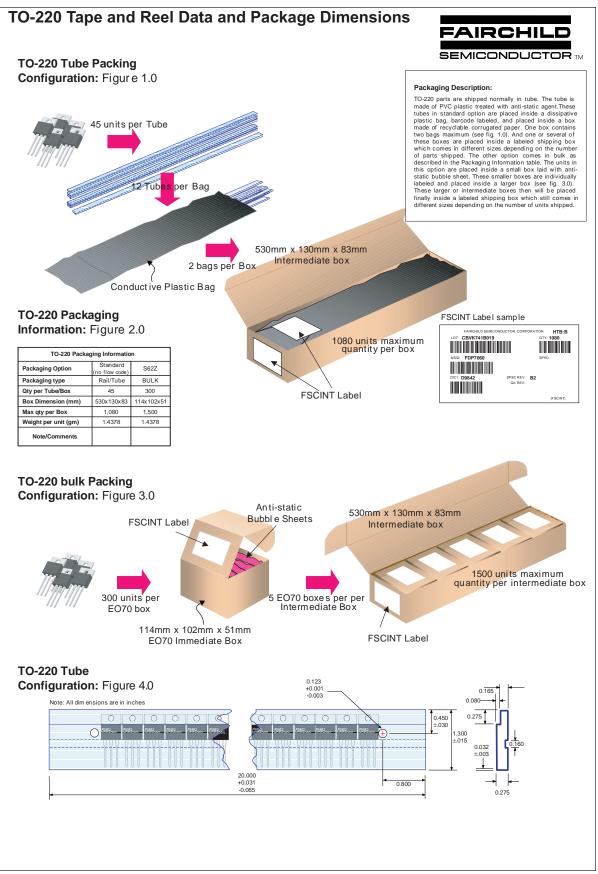
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
DRAIN-S	OURCE AVALANCHE RAT	NGS (Note 1)				
W _{DSS}	Single Pulse Drain-Source	$V_{DD} = 15 \text{ V}, I_D = 40 \text{ A}$			150	mJ
AR	Avalanche Energy Maximum Drain-Source Avalnche	L Current			40	A
					40	~
Off Chara BV _{DSS}	acteristics Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
	Breakdown Voltage Temperature	$V_{GS} = 0.0$, $I_D = 250 \mu$ A $I_D = 250 \mu$ A, Referenced to 25° C		23		mV/°C
ΔT_{J}	Coefficient					
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
GSSF	Gate-Body Leakage Current, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage Current, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Chara	acteristics (Note 1)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	1	1.6	3	V
$\Delta V_{GS(th)}$ ΔT_{\perp}	Gate Threshold Voltage Temperature Coefficient	I_D = 250 µA, Referenced to 25°C		-4.5		mV/°C
R _{DS(on)}	Static Drain-Source	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A},$		0.015	0.018	Ω
	On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}, T_J = 125^{\circ}\text{C}$		0.021	0.030	
D(on)	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, I_D = 17 \text{ A}$ $V_{GS} = 10 \text{ V}, V_{DS} = 10 \text{ V}$	40	0.019	0.024	A
g _{FS}	Forward Transconductance	$V_{DS} = 5 V, I_D = 20 A$	10	30		s
<u>Dynamic</u> C _{iss}	Characteristics	V _{DS} = 15 V, V _{GS} = 0 V,		1160		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		250		pF
C _{rss}	Reverse Transfer Capacitance			100		pF
	g Characteristics (Note 1) Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \text{ I}_{D} = 1 \text{ A},$		9	17	ns
t _{d(on)} t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		11	20	ns
t _{d(off)}	Turn-Off Delay Time			23	37	ns
t _f	Turn-Off Fall Time			8	16	ns
Q _g	Total Gate Charge	V _{DS} = 15 V,		12	10	nC
Q _{gs}	Gate-Source Charge	$I_{\rm D} = 20$ A, $V_{\rm GS} = 5$ V		3.2		nC
Q _{gd}	Gate-Drain Charge			3.7		nC
	una Diada Okanastariatian	and Maximum Datin na				
<u>Drain-So</u> Is	urce Diode Characteristics Maximum Continuous Drain-Source				40	A
V _{SD}	Drain-Source Diode Forward	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 20 \text{ A}$ (Note 1)		0.95	1.2	V
	Voltage	$V_{GS} = 0 V, I_{S} = 20 A$ (Note 1)		0.55	1.2	v

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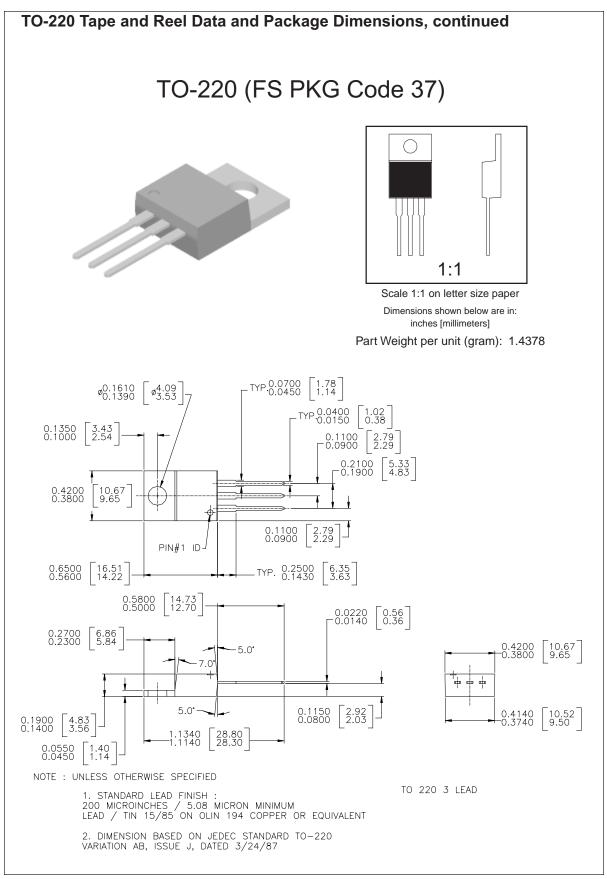


FDP6030BL/FDB6030BL Rev.C

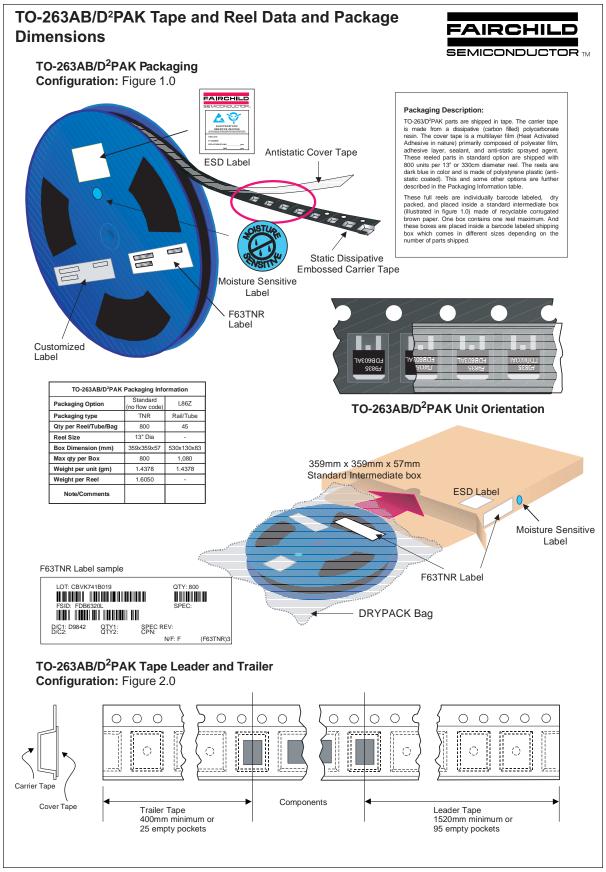




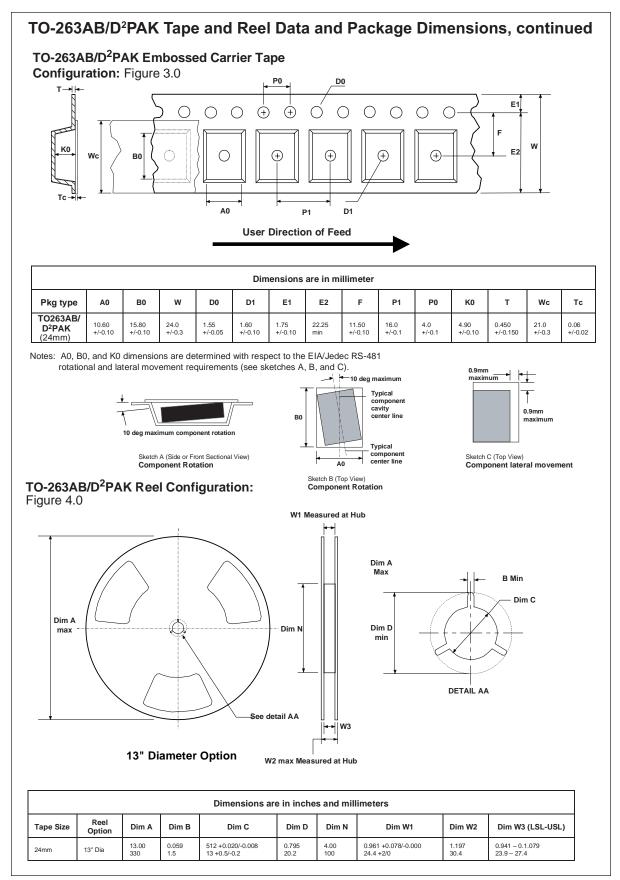
August 1999, Rev. B

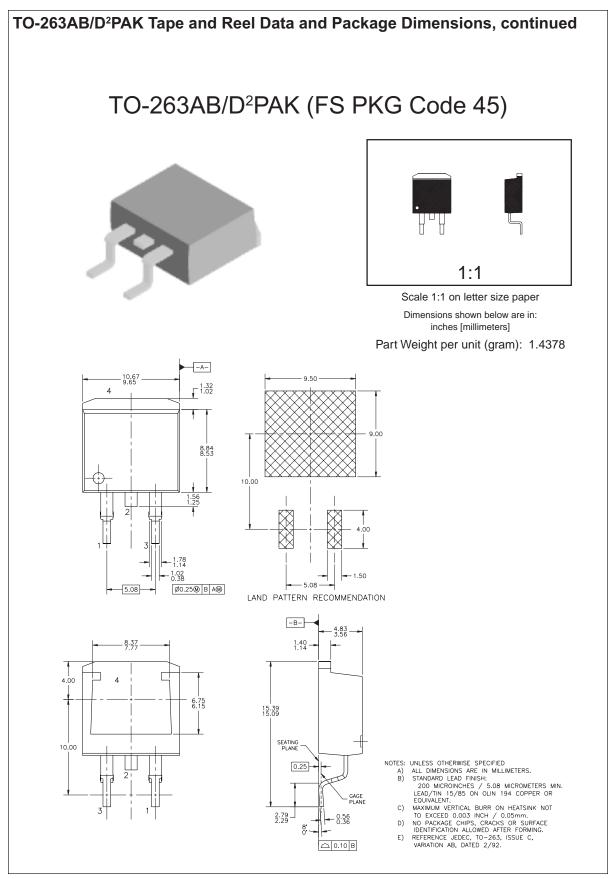


September 1998, Rev. A



September 1999, Rev. B





August 1998, Rev. A

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